

APPLICATION
FOR
UNITED STATES LETTERS PATENT

TITLE: PASS/FAIL BATTERY INDICATOR

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I hereby certify under 37 CFR §1.10 that this correspondence is being deposited with the United States Postal Service as Express Mail Post Office to Addressee with sufficient postage on the date indicated below and is addressed to the Commissioner for Patents, Washington, D.C. 20231.

August 30, 2001
Date of Deposit
Samantha Bell
Signature
Samantha Bell
Typed or Printed Name of Person Signing Certificate

Office Action Summary	Application No.	Applicant(s)	
	10/684,538	MATSUI, GANTETSU	
	Examiner Henry N. Tran	Art Unit 2629	

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --
Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) Responsive to communication(s) filed on 14 October 2003.
- 2a) This action is **FINAL**. 2b) This action is non-final.
- 3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) Claim(s) 1-11 is/are pending in the application.
- 4a) Of the above claim(s) _____ is/are withdrawn from consideration.
- 5) Claim(s) 10 and 11 is/are allowed.
- 6) Claim(s) 1 is/are rejected.
- 7) Claim(s) 2-9 is/are objected to.
- 8) Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) The specification is objected to by the Examiner.
- 10) The drawing(s) filed on 14 October 2003 is/are: a) accepted or b) objected to by the Examiner.
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
- 11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

- 12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) All b) Some * c) None of:
 1. Certified copies of the priority documents have been received.
 2. Certified copies of the priority documents have been received in Application No. _____.
 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

* See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

- 1) Notice of References Cited (PTO-892)
- 2) Notice of Draftsperson's Patent Drawing Review (PTO-948)
- 3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)
Paper No(s)/Mail Date 2/8/06 and 3/22/04.
- 4) Interview Summary (PTO-413)
Paper No(s)/Mail Date. _____.
- 5) Notice of Informal Patent Application (PTO-152)
- 6) Other: _____.

DETAILED ACTION

This Application has been examined. The Preliminary Amendment received 10/14/03 has been entered. The original claims 1-11 are pending. The examination results are as follows.

Priority

1. Receipt is acknowledged of papers submitted under 35 U.S.C. 119(a)-(d), which papers have been placed of record in the file.

Information Disclosure Statement

2. The examiner has considered the documents listed in forms PTO-1449 submitted with the Information Disclosure Statements (IDSs) received 2/8/06 and 3/22/04 (see the attached forms PTO-1449).

Drawings

3. The drawings are objected to under 37 CFR 1.83(a). The drawings must show every feature of the invention specified in the claims. Therefore, the: “an operation unit” (claim 1), “an average value calculating subunit”, “a threshold calculating subunit” and “a setting subunit” (claim 3) must be shown or the features canceled from the claims. No new matter should be entered.

Corrected drawing sheets in compliance with 37 CFR 1.121(d) are required in reply to the Office action to avoid abandonment of the application. Any amended replacement drawing sheet should include all of the figures appearing on the immediate prior version of the sheet, even if only one figure is being amended. The figure or figure number of an amended drawing should not be labeled as “amended.” If a drawing figure is to be canceled, the appropriate figure

must be removed from the replacement sheet, and where necessary, the remaining figures must be renumbered and appropriate changes made to the brief description of the several views of the drawings for consistency. Additional replacement sheets may be necessary to show the renumbering of the remaining figures. Each drawing sheet submitted after the filing date of an application must be labeled in the top margin as either "Replacement Sheet" or "New Sheet" pursuant to 37 CFR 1.121(d). If the changes are not accepted by the examiner, the applicant will be notified and informed of any required corrective action in the next Office action. The objection to the drawings will not be held in abeyance.

Specification

4. The specification is objected to as failing to provide proper antecedent basis for the claimed subject matter. See 37 CFR 1.75(d)(1) and MPEP § 608.01(o). The claim term: "an operation unit" recited in claim 1 has no clear descriptive support in the specification and the drawings.

Correction of the above is required in response to this Office action.

Claim Rejections - 35 USC § 102

5. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless –

(e) the invention was described in a patent granted on an application for patent by another filed in the United States before the invention thereof by the applicant for patent, or on an international application by another who has fulfilled the requirements of paragraphs (1), (2), and (4) of section 371(c) of this title before the invention thereof by the applicant for patent.

The changes made to 35 U.S.C. 102(e) by the American Inventors Protection Act of 1999 (AIPA) and the Intellectual Property and High Technology Technical Amendments Act of 2002

do not apply when the reference is a U.S. patent resulting directly or indirectly from an international application filed before November 29, 2000. Therefore, the prior art date of the reference is determined under 35 U.S.C. 102(e) prior to the amendment by the AIPA (pre-AIPA 35 U.S.C. 102(e)).

6. Claim 1 is rejected under 35 U.S.C. 102(e) as being anticipated by Sakurai et al (U.S. Patent No. 6,369,794).

Sakurai et al, Figs. 1-3, teach an operation instructing device comprising: an area setting unit (102, 103) operable to set a movement detection area for a specific user, based on motion values resulting from movements unique to the user; and an operation unit (308) operable to activate the area setting unit in response to an operation by the user (Sakurai et al teach that a user operates an operation indication outputting device that comprises a motion analyzing unit (102) and a user action analyzing unit (103) as an areas setting unit to set a movement detection area defined by predetermined threshold values (ThHigh and ThLow) and based on motion values (“acceleration levels”), and an operation start button (308) is pressed to activate the a motion analyzing unit (102) and a user action analyzing unit (103); see also Figs. 5-7; and col. 7, line 34 to col. 11, line 21.

Allowable Subject Matter

7. Claims 10 and 11 are allowed.
8. Claims 2-9 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

Conclusion

9. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. They are U.S. Patents Nos.: 6798429, 6567101, 6466197 and 6347290, and U.S. Publication No.: US 2004/0169636 A1, which teach instructing input devices which utilize user's motions or gestures detected by motion sensors.
10. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Henry N. Tran whose telephone number is 571-272-7760. The examiner can normally be reached on M-F 8:00-4:30.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, BIPIN H. SHALWALA can be reached on 571-272-7681. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

HT
5/29/06

Henry N. Tran
HENRY N. TRAN
PRIMARY EXAMINER

Referring now to FIG. 3, a metal-insulator-metal diode 40 is shown. The metal-insulator-metal diode 40 includes a first electrode 42, e.g., a copper foil substrate or another conductive material such as carbon or gold or other conductive materials such as chromium, tungsten, molybdenum, or other conductive materials such as metal particles dispersed in a polymer binder such as a conductive ink. The metal-insulator-metal diode 40 further includes a composite metal-insulator layer 44 comprised of metal particles 50 suspended in a dielectric binding layer 52. As shown in FIG. 3A, the metal particles 50 have an intrinsic oxide layer 50a that covers the surface of the particles 50. One preferred metal is tantalum that readily forms an intrinsic, stable and generally uniform intrinsic oxide layer 50a. Other metals can be used such as niobium. These other metals should form oxides that are self-limiting, stable, and having a suitable dielectric constant for the application. One reason that tantalum is preferred is that the intrinsic oxide layer forms readily on tantalum upon its exposure to air.

Disposed on the composite metal-insulating layer 44 is a second electrode 46 also comprised of e.g., copper or another conductive materials such as a carbon, chromium, tungsten, molybdenum, or gold or other conductive materials. The second electrode is preferably disposed directly on the layer 42 to be in contact with the intrinsic oxide layer 50a on the particles 50. The second electrode also can be a composite layer including the conductive materials and a binder. By varying the conductivity of the electrode layer 46, the electrical characteristics of the device 40 can be changed. Specifically, the I-V characteristic curve can be made sharper to obtain a steeper on/off characteristic. That is, the higher the electrical conductivity, the sharper the curve.

As will be described below in FIGS. 7A-7D, the M-I-M

device has a symmetrical current-voltage (I-V) characteristic curve exhibiting diode-like properties. The device also can be made to have lower switching voltages than other approaches, e.g., less than 10 volts and more specifically less than 1 volt to about 0.5 volts but with the same symmetrical properties. By varying the ratio of the tantalum to the binder and also the thickness of the tantalum-binder layer enables shifting of the I-V characteristic curve for the same material up or down within a range of plus/minus 50% or more.

The switching voltage of the device 40 can be more consistent from device to device. This may occur due in part to the more consistent oxide layer thickness and quality of the intrinsically formed oxide. The thickness of the tantalum oxide layer 50a does not vary widely compared to thermal annealing or anodized oxide layers. It is believed that the intrinsic layer 50a also has a substantially uniform thickness from tantalum particle 50 to tantalum particle 50 that is on the order of monolayers of thickness. Characteristics of the tantalum particles are that the powder has a particle size in a range less than 0.5 microns up to about 10's of microns. The printed layer 44 can have a thickness less than 0.5 mils up to 8-10 mils. Other particle sizes and thicknesses could be used herein.

Referring now to FIG. 4, another embodiment 40' of the diode includes a layer 44' comprising inert particles 54 (as shown in FIG. 4A) of another dielectric material such as particles 54 of titanium dioxide TiO_2 or magnesium carbonate $MgCO_3$ dispersed within the polymer binder 52 and the tantalum particles 50 having an oxide layer 50a. In this embodiment, a portion (e.g., 0% to 75%) of the tantalum particles 50 are replaced with inert dielectric material particles 54 such as the titanium dioxide or magnesium carbonate. The tantalum particles 50 can optionally have an annealed oxide or other type of oxide

layer disposed about the tantalum although, the intrinsic oxide layer 50a alone is preferred.

5 The addition of dielectric particles of e.g., titanium dioxide solids to the polymer binder 52 and the tantalum particles 50 can improve printing of the layer 44', enabling use of lower amounts of tantalum particles while still maintaining a high solids content that would exhibit good diode properties. This would be particularly desirable with very thin layers of the metal/insulating material layer to avoid shorting of the two 10 electrodes 42 and 46 through the layer 44'. Including an inert material reduces the probability of shorting and provides a more consistent film/coating.

15 Moreover, at sufficiently low concentrations of tantalum, devices may be provided with higher switching voltages. It is anticipated that rather than using the oxide layer around the tantalum particles to act as the insulator, i.e., the potential barrier that electrons need to exceed in order to cause conduction, the barrier would be governed by the dielectric properties of the inert material, e.g., the titanium dioxide and the binder at the lower concentrations of tantalum.

20 Referring now to FIG. 5, another embodiment 40" of the diode has the first electrode 42 and the metal-insulating layer 44 or 44' on the first electrode. This structure 40" may give similar diode properties when a connection 58 is made to the metal-insulating layer 44 or 44'. By eliminating the second electrode, the device 40" can have fewer layers, changing the 25 fabrication process without substantially altering the characteristics of the metal insulator layer.

30 Referring now to FIG. 6, the device of FIG. 3 can be prepared as follows: The process 60 includes mixing 62 tantalum powder that is 99.97% pure, having the intrinsic oxide layer and having a particle size less than e.g., 5 microns, with a polymer

binder such as Acheson, Electrodag No. 23DD146A, or Acheson SS24686, a more thixotropic material. Both polymer binders are available from Acheson, Port Huron, MI. Other binders can be used with the tantalum to form a tantalum ink. The binders should be electrically insulating, stable with tantalum or the other metal used and preferably have an relatively high e.g., 15% to 35% or so solids content. The tantalum can be in a range of 100% to 39% of the total weight of the binder. Other ranges could be used. The tantalum particles and binder are mixed well to produce the tantalum ink. The tantalum ink is printed 64 on the first electrode e.g., a copper foil substrate or on other conductive material. The layer is printed, for example, by either draw down bars, screen printing, flexo or gravure printing techniques. The layer is dried 66, e.g., in an oven at 120°C for 15-20 minutes. A second conductive layer such as chromium in the form of chromium particles mixed in a binder material is printed 68 on the tantalum binder layer. This chromium layer is also dried 40 at e.g., at 120 °C for 15-20 minutes producing the device 40. Thereafter, the device 40 can be tested 42.

Alternative conductive layers or metals such as copper, tungsten, molybdenum, carbon and so forth can be used for the first and/or second electrode. The conductivity of this layer can be varied by changing relative concentrations of conductive material to binder. Exemplary ranges for conductive material are 30% to 39%. By varying the conductivity of this layer, the shape of the current-voltage characteristic curve can be varied, making it a little sharper producing a diode having a steeper on/off response.

Processing is simplified because the tantalum particles used have an intrinsic oxide layer 50a. There is no need to thermally anneal or otherwise thermally preprocess the tantalum powder. The intrinsic oxide coating is very consistent in

thickness and quality. This tends to produce very consistent metal-insulator layer materials and hence diodes with switching voltages having relatively low standard deviations over a series of diodes.

5 Another advantage is that since there is no need to thermally anneal the tantalum powder, the properties of the ink can be adjusted to achieve various diode properties to fit different applications. Ink formulation may be an easier process to control than thermal processing of the tantalum.

10 This device could also be referred to as a varistor, i.e., a thin printed varistor. This M-I-M structure is good for applications that need a nonlinear element that operates at low voltages and perhaps low current that can be printed rather than using semiconductor deposition techniques.

15 Referring now to FIGS. 7A-7D plots of voltage vs. current showing typical switching characteristics of M-I-M diode devices of FIGS. 3-6 are shown. As shown in FIG. 7A, a current voltage characteristic curve 74 for a M-I-M diode device exhibits a switching voltage at 100 na. (nano-amperes) of approximately 1.8 volts, with an on/off ratio that is calculated to be about 33. The current voltage characteristic curve 74 was obtained using a Hewlett Packard semiconductor analyzer, Model No. 4155B.

20 This device used a tantalum layer that was prepared by mixing 5 grams of tantalum particles obtained from Alfa Aesar, Ward Hill, MA. having a particle diameter of less than 2 microns, with 20 grams of Electrodag 23DD146A polymer having a 25% solid versus 75% volatile compound composition. The ink was coated onto a conductive surface of copper foil using a 15 mil cutout i.e., to produce a layer having a wet thickness of 15 mils. The sample was dried in an oven at 120°C for 20 minutes. The ink for the second layer of the diode was prepared by mixing 5 grams of chromium powder with a particle size of less than 5 microns as

received from Alfa Aesar, with 4 grams of Electrodag 23DD146A and was coated on top of the tantalum ink layer using a 5 mil cutout. This coating was dried for 20 minutes at 120°C.

As shown in FIG. 7B, the M-I-M diodes can exhibit different switching voltages based upon different "P:B" ratios, that is, different ratios of metal (e.g., tantalum) particles to binder. As shown in FIG. 7B, for the same thickness of 15 mils, with P:B ratios of 5, 2, and 1, devices exhibit switching voltages of approximately 9 volts (curve 75a), 5.3 volts (curve 75b) and 3.8 volts (curve 75c) at 100 nano amperes.

As also shown in FIG. 7C, varying the wet thickness of the tantalum layer can also produce varying switching voltages. With a tantalum layer having a tantalum to binder ratio (P:B) of 8:1, a M-I-M diode having a 15 mil thick tantalum layer would exhibit a switching voltage of approximately 9 volts (curve 76a), a 10 mil thick layer would provide a M-I-M diode with a switching voltage of approximately 7.8 volts (curve 76b), and a 5 mil thick layer would provide a M-I-M diode with a switching voltage of approximately 4.6 volts (curve 76b). Each of the switching voltages are measured at 100 nano amperes.

Referring now to FIG. 7D, addition of magnesium carbonate to the tantalum layer can produce M-I-M diodes that have consistently high on/off ratios with minimal impact on switching voltage. As shown in FIG. 7D, as the amount of magnesium carbonate is increased, the switching voltage characteristic becomes steeper. The curve 76a shows the switching characteristic for a 100% tantalum layer having a P:B ratio of 1:1 that exhibits a switching voltage of 1.8 volts. Curves 77b-77d illustrate that as the amount of magnesium carbonate increases, the switching characteristic becomes steeper therefore indicating a better on/off ratio.

Other Embodiments

It is to be understood that while the invention has been described in conjunction with the detailed description thereof, the foregoing description is intended to illustrate and 5 not limit the scope of the invention, which is defined by the scope of the appended claims. Other aspects, advantages, and modifications are within the scope of the following claims.

What is claimed is: